N-Channel 200-V (D-S) MOSFET

GENERAL DESCRIPTION

The ME2620-G is the N-Channel logic enhancement mode power field effect transistors, using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on state resistance. These devices are particularly suited for low voltage application such as cellular phone, notebook computer power management and other battery powered circuits, and low in-line power loss that are needed in a very small outline surface mount package.

FEATURES

- $R_{DS(ON)} \leqq 756m\Omega @ V_{GS}=10V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability

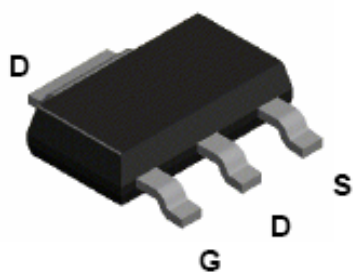
APPLICATIONS

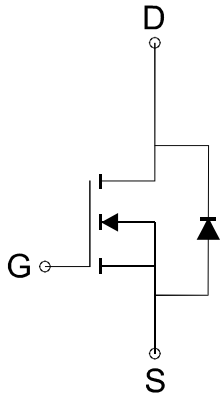
- Power Management in Note book
- DC/DC Converter
- Load Switch
- LCD Display inverter

PIN CONFIGURATION

(SOT-223)

Top View





N-Channel MOSFET

Ordering Information: ME2620-G (Green product-Halogen free)

Absolute Maximum Ratings (T_A=25℃ Unless Otherwise Noted)

Parameter		Symbol	Maximum Ratings	Unit
Drain-Source Voltage		V_{DS}	200	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_A=25℃	I_D	1.4	A
	T_A=70℃		1.1	
Pulsed Drain Current		I_{DM}	5	A
Maximum Power Dissipation	T_A=25℃	P_D	2.2	W
	T_A=70℃		1.4	
Operating Junction and Storage Temperature Range		TJ, Tstg	-55 to 150	℃
Thermal Resistance, Junction-to-Ambient *		$R_{\theta JA}$	57	℃/W

* The device mounted on 1in^2 FR4 board with 2 oz copper

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Electrical Characteristics (T_A =25℃ Unless Otherwise Specified)

Symbol	Parameter	Limit	Min	Typ	Max	Unit
STATIC						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	200			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	2		4	V
I_{GSS}	Gate Leakage Current	V_{DS}=0V, V_{GS}=±20V			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=200V, V_{GS}=0V			1	μA
$R_{DS(ON)}$	Drain-Source On-Resistance [a]	V_{GS}=10V, I_D= 1.4A		630	756	mΩ
V_{SD}	Diode Forward Voltage	I_S=1A, V_{GS}=0V			1.2	V
DYNAMIC						
Qg	Total Gate Charge	V_{DS}=100V, V_{GS}=10V, I_D=1.4A		14.3		nC
Qgs	Gate-Source Charge			4.3		
Qgd	Gate-Drain Charge			5		
Ciss	Input Capacitance	VDS=25V, VGS=0V,f=1MHz		583		pF
Coss	Output Capacitance			27		
Crss	Reverse Transfer Capacitance			6		
td(on)	Turn-On Delay Time	VDS=100V, RL =71.4Ω, VGS=10V, RG=4.7Ω ID=1.4A		6.2		ns
tr	Turn-On Rise Time			21.4		
td(off)	Turn-Off Delay Time			19.5		
tf	Turn-Off Fall Time			27.3		

Notes: a. Pulse test: pulse width≦ 300us, duty cycle≦ 2%, Guaranteed by design, not subject to production testing.

b. Matsuki Electric/ Force mos reserves the right to improve product design, functions and reliability without notice.

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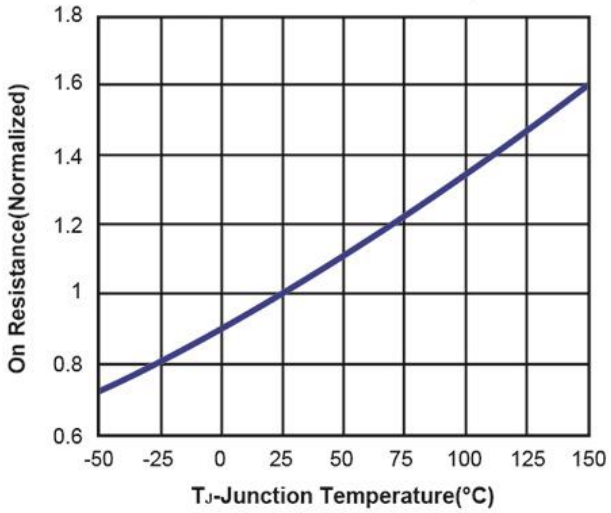
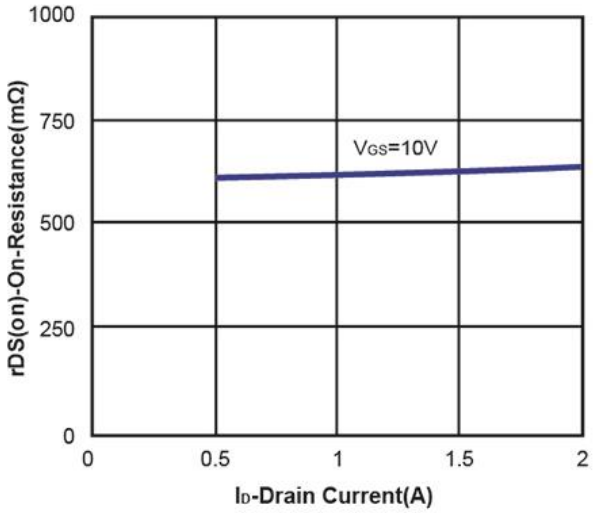
Typical Characteristics (T_J =25℃ Noted)

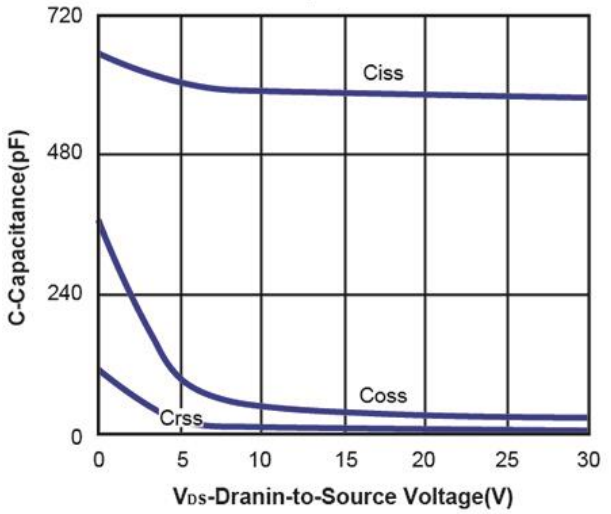
On Resistance vs. Junction Temperature



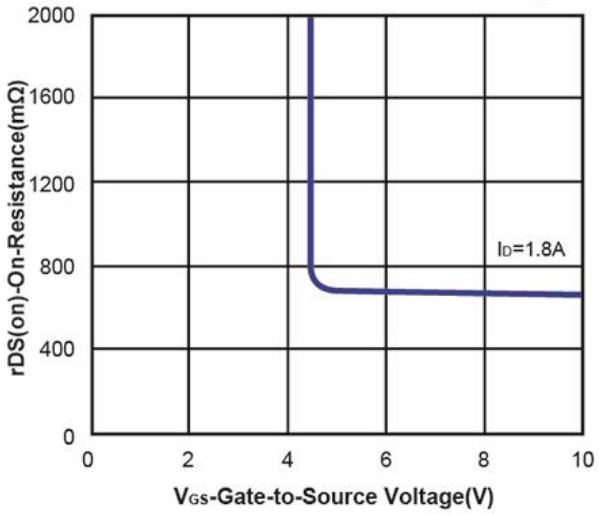
On Resistance vs. Drain Current



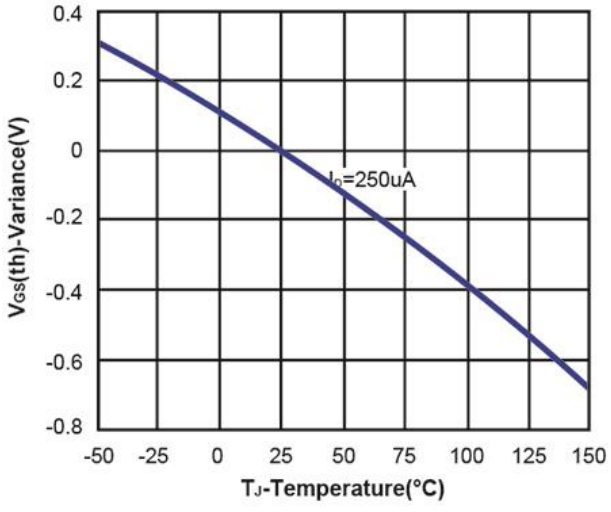
Capacitance



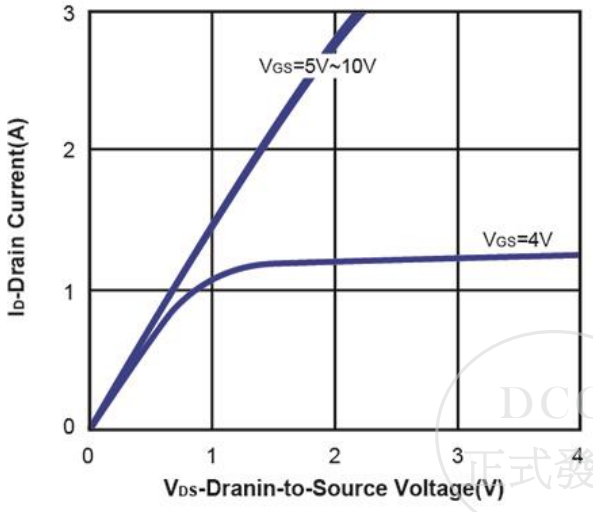
On Resistance vs. Gate-to-Source Voltage



Threshold Voltage



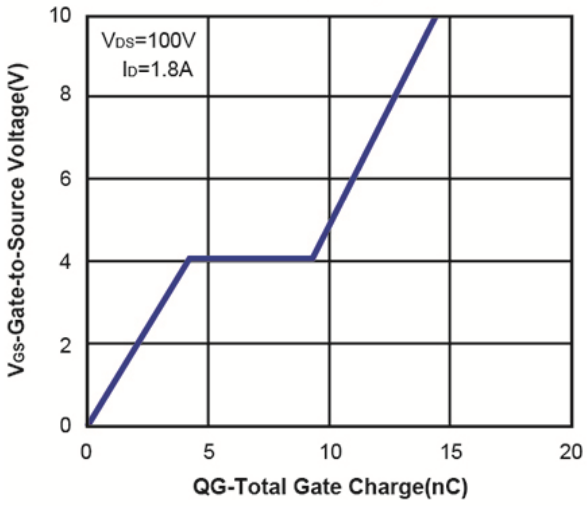
On-Region Characteristics



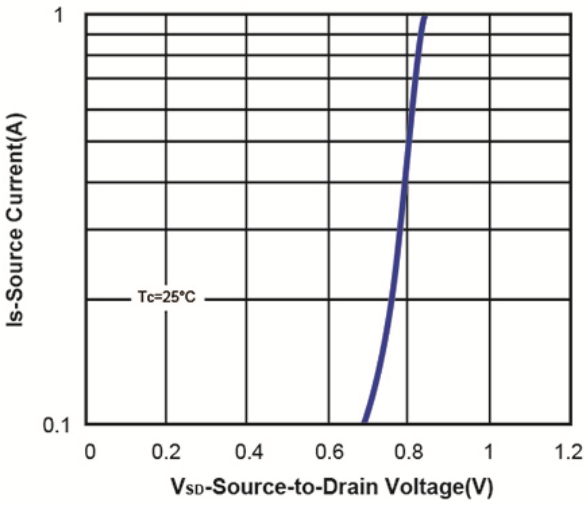
N-Channel 200-V (D-S) MOSFET

Typical Characteristics (T_J =25℃ Noted)

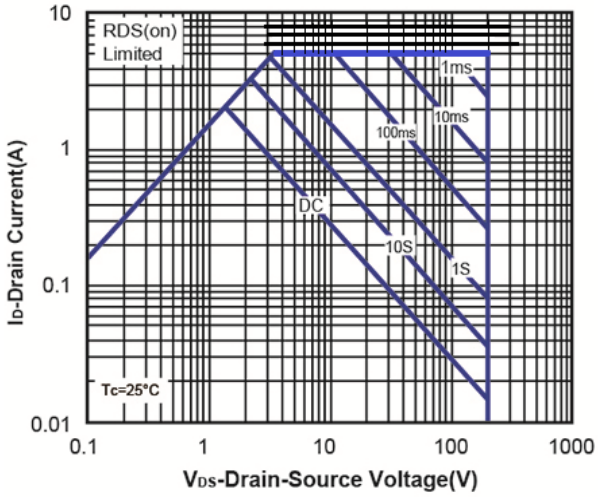
Gate Charge



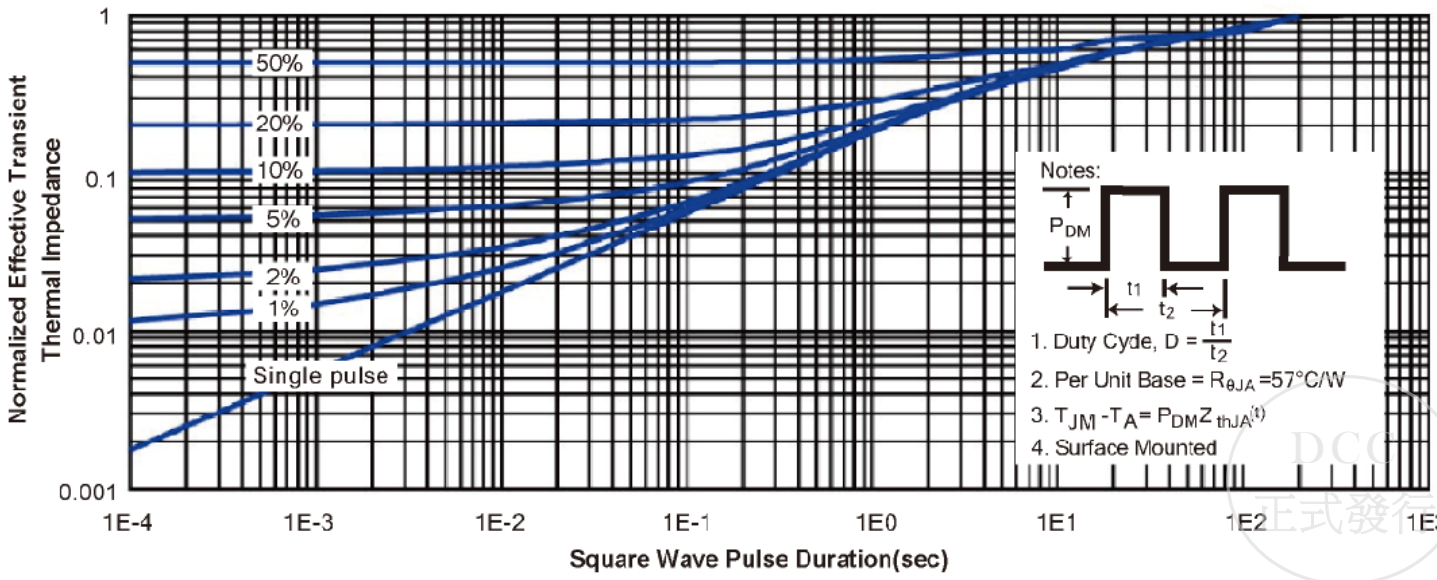
Body-diode characteristics



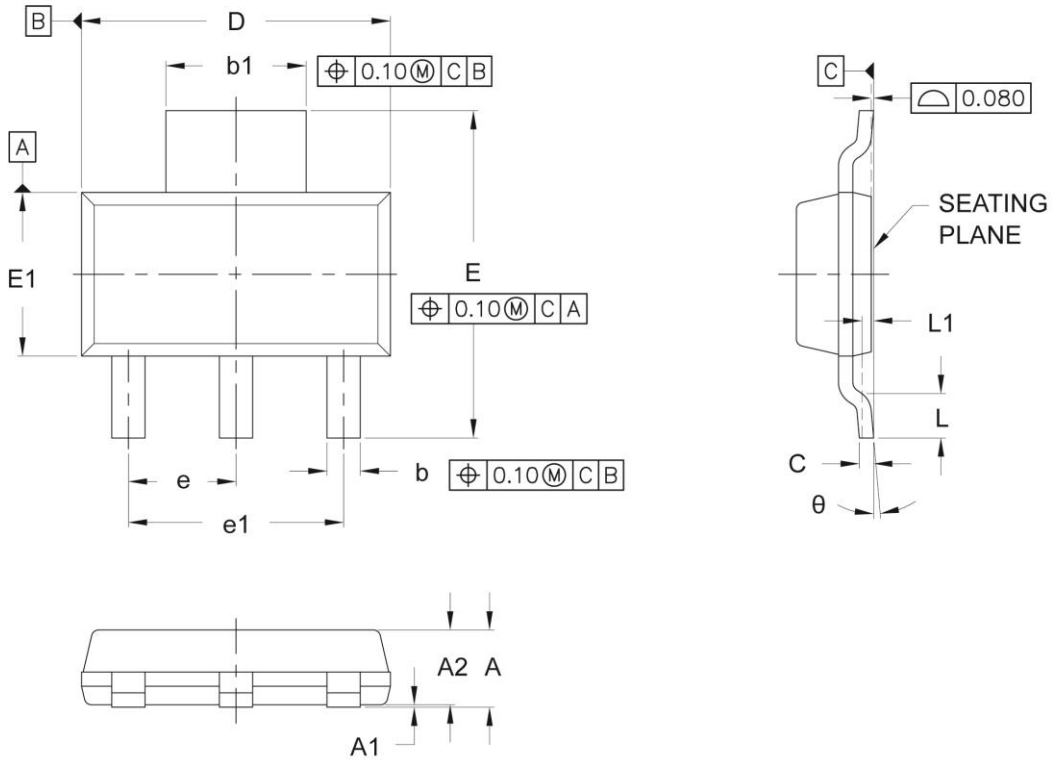
Maximum Forward Biased Safe Operating Area



Normalized Thermal Transient Impedance,Junction-to-Ambient



SOT-223 Package Outline



SYMBOL	COMMON					
	DIMENSIONS MILLIMETER			DIMENSIONS INCH		
	MIN.	MOM.	MAX.	MIN.	MOM.	MAX.
A	—	—	1.80	—	—	0.0709
A1	0.02	—	0.10	0.0008	—	0.0039
A2	1.50	1.60	1.70	0.0591	0.0630	0.0669
b	0.66	0.76	0.84	0.0260	0.0300	0.0330
b1	2.90	3.00	3.10	0.1142	0.1181	0.1220
C	0.23	0.30	0.35	0.0090	0.1181	0.1378
D	6.30	6.50	6.70	0.2480	0.2560	0.2638
E	6.70	7.00	7.30	0.2638	0.2760	0.2874
E1	3.30	3.50	3.70	0.1300	0.1378	0.1457
e	2.30 BSC			0.0906 BSC		
e1	4.60 BSC			0.1811 BSC		
L	0.75	—	—	0.0295	—	—
θ	0°	—	10°	0°	—	10°